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(54) **Title**: A METHOD OF FABRICATING A MULTILAYER STRUCTURE WITH CIRCUIT LAYER TRANSFER

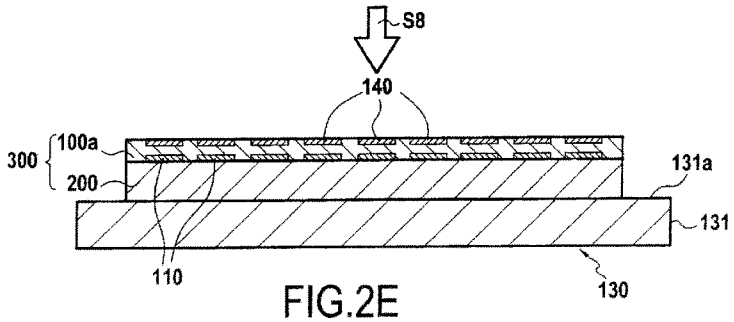


FIG.2E

(57) **Abstract**: A method of producing a composite structure comprises a step of producing a first layer of microcomponents (110) on one face of a first substrate (100), the first substrate being held flush against a holding surface (121a) of a first support (121) during production of said microcomponents (110), and a step of bonding the face of the first substrate (100) comprising the layer of microcomponents (110) onto a second substrate (200). During the bonding step, the first substrate (100) is held flush against a second support (221) the holding surface (221a) of which has a flatness that is less than or equal to that of the first support (120) used during production of the first layer of microcomponents (110).

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